

SKiiP 232 GD 120 - 313 CTV

Absolute Maximum Ratings			
Symbol	Conditions ¹⁾	Values	Units
$V_{\text{isol}}^{4)}$	AC, 1min	3000	V
$T_{\text{op}}, T_{\text{stg}}$	Operating / stor. temperature	-25...+85	°C
IGBT and Inverse Diode			
V_{CES}		1200	V
$V_{\text{CC}}^{5)}$	Operating DC link voltage	900	V
I_{C}	IGBT	200	A
$T_j^{3)}$	IGBT + Diode	-40...+150	°C
I_F	Diode	200	A
I_{FM}	Diode, $t_p < 1 \text{ ms}$	400	A
I_{FSM}	Diode, $T_j = 150 \text{ °C}, 10\text{ms}; \sin$	1440	A
I^2t (Diode)	Diode, $T_j = 150 \text{ °C}, 10\text{ms}$	10	kAs ²
Driver			
V_{S1}	Stabilized Power Supply	18	V
V_{S2}	Non-stabilized Power Supply	30	V
f_{smax}	Switching frequency	20	kHz
dV/dt	Primary to secondary side	75	kV/μs

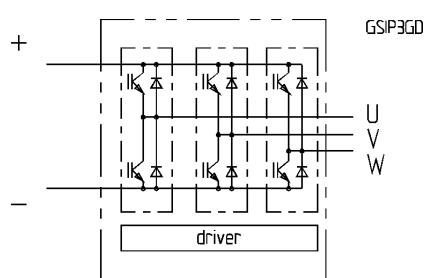
Characteristics					
Symbol	Conditions ¹⁾	min.	typ.	max.	Units
IGBT ¹¹⁾					
$V_{(\text{BR})\text{CES}}$	Driver without supply	$\geq V_{\text{CES}}$	—	—	V
I_{CES}	$V_{\text{GE}} = 0, T_j = 25 \text{ °C}$	—	—	0,4	mA
	$V_{\text{CE}} = V_{\text{CES}}, T_j = 125 \text{ °C}$	—	10	—	mA
V_{TO}	$T_j = 125 \text{ °C}$	—	—	1,38	V
r_T	$T_j = 125 \text{ °C}$	—	—	10,5	mΩ
V_{Cesat}	$I_{\text{C}} = 175\text{A}, T_j = 125 \text{ °C}$	—	—	3,2	V
V_{Cesat}	$I_{\text{C}} = 175\text{A}, T_j = 25 \text{ °C}$	—	—	3,05	V
$E_{\text{on}} + E_{\text{off}}$	$V_{\text{CC}}=600/900\text{V}, I_{\text{C}}=200\text{A}$ $T_j = 125 \text{ °C}$	—	—	60/98	mJ
C_{CHC}	per Phase, AC side	—	1,4	—	nF
L_{CE}	Top, Bottom	—	15	—	nH
Inverse Diode ²⁾					
$V_F = V_{\text{EC}}$	$I_F = 175\text{A}; T_j = 125 \text{ °C}$	—	—	2,45	V
$V_F = V_{\text{EC}}$	$I_F = 175\text{A}; T_j = 25 \text{ °C}$	—	—	2,55	V
$E_{\text{on}} + E_{\text{off}}$	$I_F = 200\text{A}; T_j = 125 \text{ °C}$	—	—	8	mJ
V_{TO}	$T_j = 125 \text{ °C}$	—	—	0,91	V
r_T	$T_j = 125 \text{ °C}$	—	—	5,7	mΩ
Thermal Characteristics					
$R_{\text{thjs}}^{10)}$	per IGBT	—	—	0,129	K/W
$R_{\text{thjs}}^{10)}$	per Diode	—	—	0,375	K/W
$R_{\text{thsa}}^{6,10)}$	P16 heatsink; see case S3	—	—	36	K/KW
Driver					
I_{S1}	Supply current 15V-supply	$340+360*f_s/f_{\text{smax}}+3,5*I_{\text{AC}}/A$		mA	
I_{S2}	Supply current 24V-supply	$250+250*f_s/f_{\text{smax}}+2,6*I_{\text{AC}}/A$		mA	
$t_{\text{interlock-driver}}$	Interlock-time	2,3		μs	
SKiiPPACK protection					
I_{TRIPSC}	Short circuit protection	250		A	
I_{TRIPLG}	Ground fault protection	58		A	
T_{TRIP}	Over-temp. protection	115		°C	
$U_{\text{DCTRIP}}^{9)}$	U_{DC} -protection	920		V	
Mechanical Data					
M1	DC terminals, SI Units	4	—	6	Nm
M2	AC terminals, SI Units	8	—	10	Nm

SKiiPPACK®

SK integrated intelligent
Power PACK
3-phase bridge
SKiiP

232 GD 120 - 313 CTV ^{7,9)}

Preliminary Data
Case S3



Features

- Short circuit protection, due to evaluation of current sensor signals
- Isolated power supply
- Low thermal impedance
- Optimal thermal management with integrated heatsink
- Pressure contact technology with increased power cycling capability, compact design
- Low stray inductance
- High power, small losses
- Over-temperature protection

¹⁾ $T_{\text{heatsink}} = 25 \text{ °C}$, unless otherwise specified

²⁾ CAL = Controlled Axial Lifetime Technology (soft and fast)

³⁾ without driver

⁴⁾ Driver input to DC link / AC output to DC link / AC output to heatsink

⁵⁾ with Semikron-DC link (low inductance)

⁶⁾ other heatsinks on request

⁷⁾ C - Integrated current sensors
T - Temperature protection

⁸⁾ V - 15 V or 24 V power supply options available for driver:

U - DC link voltage sense

F - Fiber optic connector

¹⁰⁾ "s" referenced to temperature sensor

¹¹⁾ NPT-technology with homogeneous current-distribution

PIN-array - 3-phase bridge driver SKiiPPACK type „GD and GDL”

X1:

Pin	signal	remark
1	shield	connected to GND, when shielded cable is used
2	BOT HB 1 IN ⁴⁾	positive 15V CMOS logic; 10 kΩ impedance
3	ERROR HB 1 OUT ¹⁾	short circuit monitoring HB1 LOW = NO ERROR; open collector output; max. 30 V / 15 mA propagation delay 1 µs, min. pulselwidth error-memory-reset 8 µs
4	TOP HB 1 IN ⁴⁾	positive 15V CMOS logic; 10 kΩ impedance
5	BOT HB 2 IN ⁴⁾	positive 15V CMOS logic; 10 kΩ impedance
6	ERROR HB 2 OUT ¹⁾	short circuit monitoring HB2 LOW = NO ERROR; open collector output; max. 30 V / 15 mA propagation delay 1 µs, min. pulselwidth error-memory-reset 8 µs
7	TOP HB 2 IN ⁴⁾	positive 15V CMOS logic; 10 kΩ impedance
8	BOT HB 3 IN ⁴⁾	positive 15V CMOS logic; 10 kΩ impedance
9	ERROR HB 3 OUT ¹⁾	short circuit monitoring HB 3 LOW = NO ERROR; open collector output; max. 30 V / 15 mA propagation delay 1 µs, min. pulselwidth error-memory-reset 8 µs
10	TOP HB 3 ⁴⁾	positive 15V CMOS logic; 10 kΩ impedance
11	Overtemp. OUT ¹⁾	LOW = NO ERROR = $\vartheta_{DCB} < 115 \pm 5^\circ C$ open collector Output; max. 30 V / 15 mA „low“ output voltage < 0,6 V „high“ output voltage max. 30 V
12	reserved	
13	U_{DC} analog OUT	U_{DC} when using option „U“ actual DC-link voltage, 9,0 V refer to U_{DCmax} max. output current 5 mA
14	+ 24 V _{DC} IN	24 V _{DC} (20 - 30 V)
15	+ 24 V _{DC} IN	don't supply with 24 V, when using + 15 V _{DC} supply voltage monitoring threshold 15,6 V
16	+ 15 V _{DC} IN	15 V _{DC} ± 4 % power supply
17	+ 15 V _{DC} IN	don't supply with 15 V, when using + 24 V _{DCIN} supply voltage monitoring threshold 13 V
18	GND	GND for power supply and
19	GND	GND for digital signals
20	Temp. analog OUT	
21	GND aux ²⁾	
22	I analog OUT HB 1	current actual value, 8,0 V refer to 100 % I_C overcurrent trip level 10 V ⇔ 125 %; I_C @ 25 °C current value > 0 ⇔ SKiiP is source current value < 0 ⇔ SKiiP is sink
23	GND aux ²⁾	
24	I analog OUT HB 2	current actual value, 8,0 V refer to 100 % I_C overcurrent trip level 10 V ⇔ 125 %; I_C @ 25 °C current value > 0 ⇔ SKiiP is source current value < 0 ⇔ SKiiP is sink
25	GND aux ²⁾	
26	I analog OUT HB 3	current actual value, 8,0 V refer to 100 % I_C overcurrent trip level 10 V ⇔ 125 %; I_C @ 25 °C current value > 0 ⇔ SKiiP is source current value < 0 ⇔ SKiiP is sink

X10: halfbridge 1 (HB1) OUT

Pin	Signal
1	
2	
8	Collector 1=TOP (HB1)
11	Gate 1=TOP (HB1)
12	Emitter 1=TOP (HB1)
13	Collector 2=BOT (HB1)
16	Gate 2=BOT (HB1)
17	Emitter 2=BOT (HB1)

X11: halfbridge 2 (HB2) OUT

Pin	Signal
1	Temp.-Sensor (HB2)1
2	Temp.-Sensor (HB2)2
8	Collector 1=TOP (HB2)
11	Gate 1=TOP (HB2)
12	Emitter 1=TOP (HB2)
13	Collector 2=BOT (HB2)
16	Gate 2=BOT (HB2)
17	Emitter 2=BOT (HB2)

X12: halfbridge 3 (HB3) OUT

Pin	Signal
1	
2	
8	Collector 1=TOP (HB3)
11	Gate 1=TOP (HB3)
12	Emitter 1=TOP (HB3)
13	Collector 2=BOT (HB3)
16	Gate 2=BOT (HB3)
17	Emitter 2=BOT (HB3)

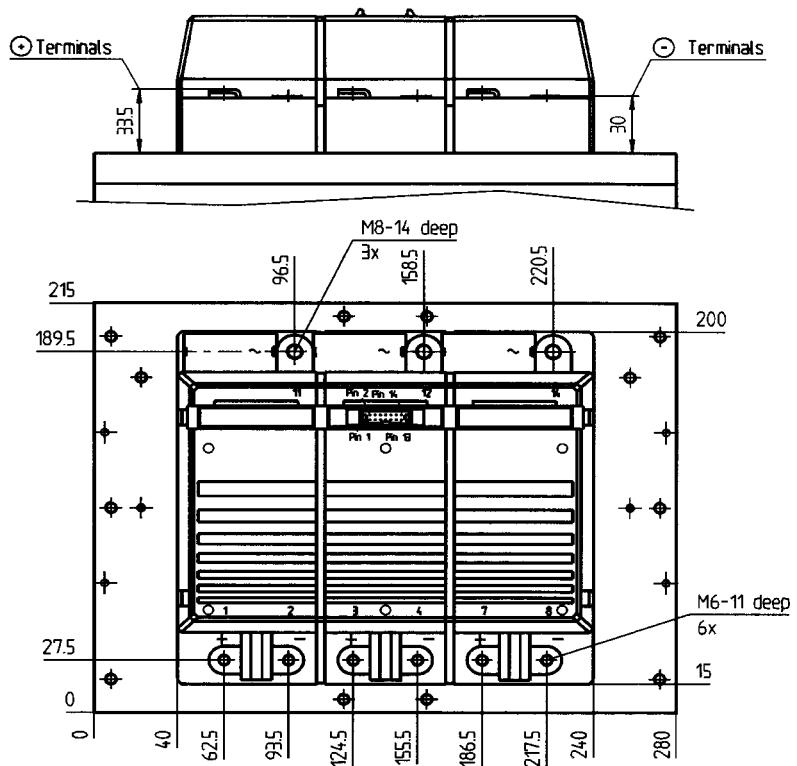
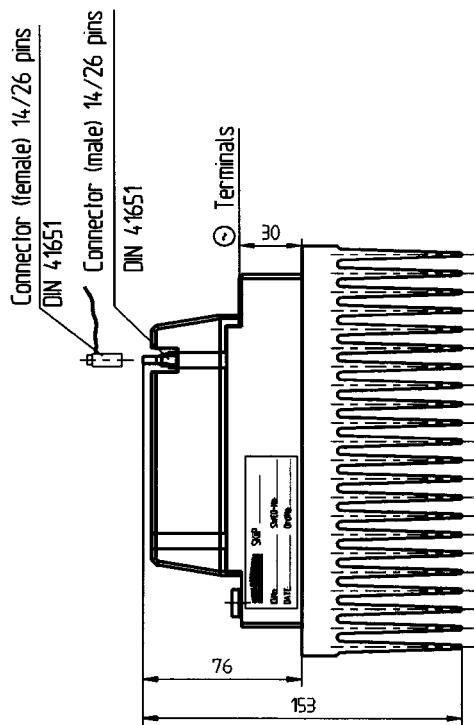
¹⁾ Open collector output, external pull up resistor necessary

²⁾ GND aux = reference for analog output signals

⁴⁾ „high“ (min) 11,2 V
„low“ (max) 5,4 V

Case S3

SKiiPPACK 3 - GB; GD



Weight without heatsink: 2,72 kg
P16:

6,6 kg

SKiiPPACK 3 - GB with F-option

